

CLAIM AMENDMENTS:

Claims 1-11 (Canceled).

Claim 12 (New): A semiconductor device, comprising:
a lower dielectric film;
an upper dielectric film formed in contact with the lower dielectric film;
a first interconnecting line having a first lower part formed in the lower dielectric film and a first upper part formed in the upper dielectric film, the first upper part making contact with the first lower part;

a second interconnecting line having a second lower part formed in the lower dielectric film and a second upper part formed in the upper dielectric film, the second upper part making contact with the second lower part;
wherein the first lower part and the second upper part have a first width;

and

the second lower part and the first upper part have a second width greater than the first width.

Claim 13 (New): The semiconductor device of claim 12, wherein the first interconnecting line and the second interconnecting line are mutually adjacent.

Claim 14 (New): The semiconductor device of claim 12, wherein the first width is constant and the second width is constant.

Claim 15 (New): The semiconductor device of claim 12, wherein the first upper part, the second upper part, the first lower part, and the second lower part are rectangular.

Claim 16 (New): The semiconductor device of claim 15, wherein the first interconnecting line and the second interconnecting line have a cross-sectional T shape.

Claim 17 (New): The semiconductor device of claim 12, wherein the first interconnecting line and the second interconnecting line have a first height and the first upper part, the second upper part, the first lower part, and the second lower part have a second height equal to half the first height.

Claim 18 (New): A method of making a semiconductor device, comprising:
forming a lower dielectric film;
forming a first lower part of a first interconnecting line in the lower dielectric film;
forming a second lower part of a second interconnecting line in the lower dielectric film;
after said first lower part and said second lower part are formed in the lower dielectric film, forming upper dielectric film in contact with the lower dielectric film;

forming a first upper part of the first interconnecting line in the upper dielectric film, the first upper part making contact with the first lower part; and forming a second upper part of the second interconnecting line in the upper dielectric film, the second upper part making contact with the second lower part; wherein the first lower part and the second upper part have a first width; and the second lower part and the first upper part have a second width greater than the first width.